



DMT35M7LFV

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
30V	5.0mΩ @ V _{GS} = 10V	76A
	8.5mΩ @ V_{GS} = 4.5V	58A

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Analog Switch

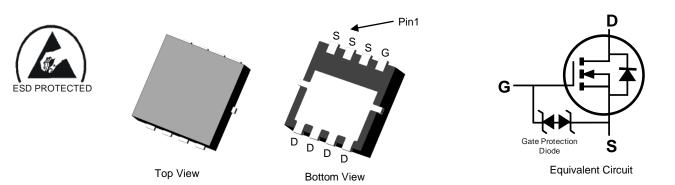
30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (Type UX)

Features

- Low R_{DS(ON)} Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



Ordering Information (Note 4)

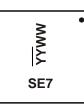
Part Number	Case	Packaging
DMT35M7LFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMT35M7LFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.</p>

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



<u>SE</u>7 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 7)	Steady State	T _C = +25°C T _C = +70°C	ID	76 61	А
Maximum Body Diode Forward Current (Note 6)			ls	2.7	А
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I _{DM}	90	A
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycle = 1%)			I _{SM}	90	A
Avalanche Current (L = 0.1mH) (Note 8)			I _{AS}	28	A
Avalanche Energy (L = 0.1mH) (Note 8)			E _{AS}	39	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	0.95	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	131	°C/W
Total Power Dissipation (Note 6)		PD	1.98	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	63	00 MM
Thermal Resistance, Junction to Case (Note 7)	R _{ejc}	2.9	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)	Cj2 Cl		• 7 P		•		
Drain-Source Breakdown Voltage	BV _{DSS}	30			V	$V_{GS} = 0V, I_{D} = 250\mu A$	
Zero Gate Voltage Drain Current (T _J = +25°C)	IDSS		—	1	μA	$V_{DS} = 24V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)						-	
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	3.6	5.0		$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		6.8	8.5	mΩ	V _{GS} = 4.5V, I _D = 16A	
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	1,667	—		$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	Coss	—	573	—	pF		
Reverse Transfer Capacitance	Crss	_	534	—			
Gate Resistance	Rg	_	0.75	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	21	—		V _{DD} = 15V, I _D = 20A	
Total Gate Charge (V _{GS} = 10V)	Qg	_	36	_	nC		
Gate-Source Charge	Qgs	_	4.8	—	nc		
Gate-Drain Charge	Q _{gd}	_	14	—			
Turn-On Delay Time	t _{D(ON)}	_	5.3	—		V_{DD} = 15V, V_{GS} = 10V, R_g = 3 Ω , I_D = 20A	
Turn-On Rise Time	t _R	_	12.3	_			
Turn-Off Delay Time	t _{D(OFF)}		18.0		ns		
Turn-Off Fall Time	tF		15.5		1	-	
Reverse Recovery Time	t _{RR}	_	16	—	ns		
Reverse Recovery Charge	Q _{RR}	—	14	—	nC	I _F = 20A, di/dt = 500A/µs	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

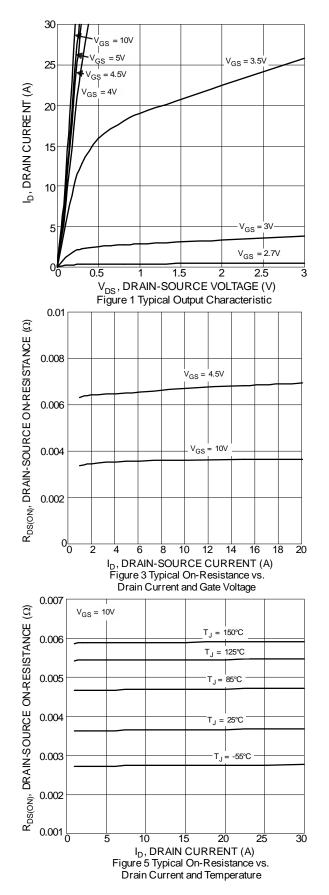
Device mounted on FR-4 to board, with minimum recommended pad layout, single stoed.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).

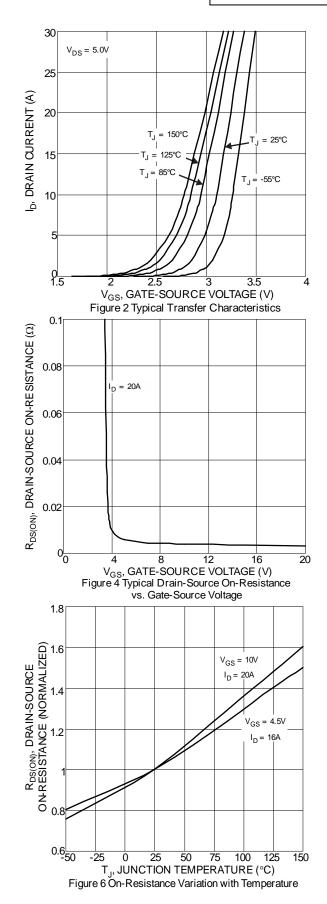
8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

9. Short duration pulse test used to minimize self-heating effect.

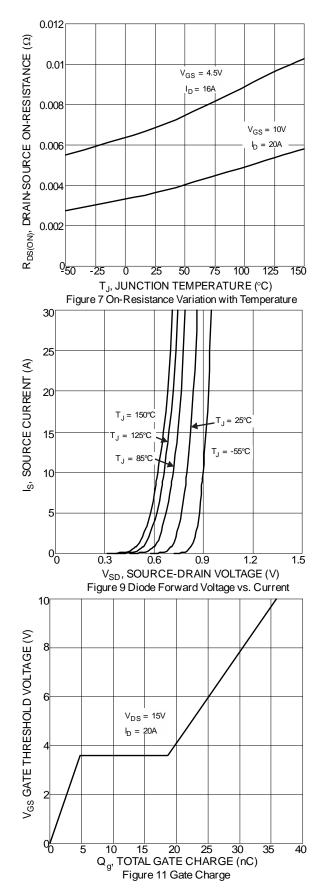
10. Guaranteed by design. Not subject to product testing.

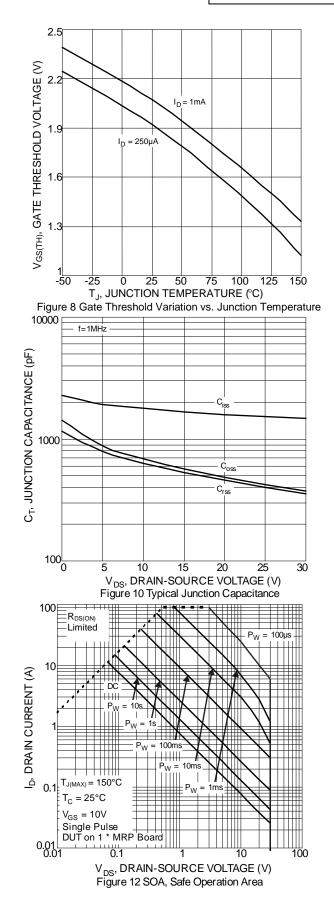




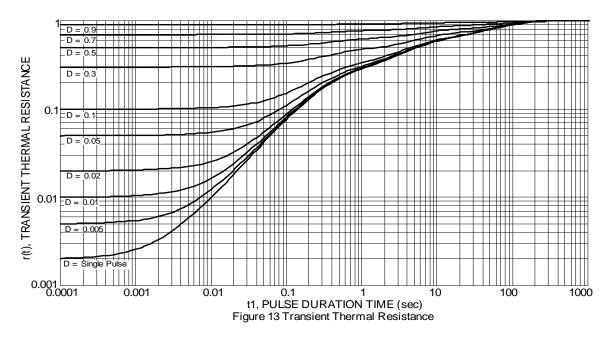








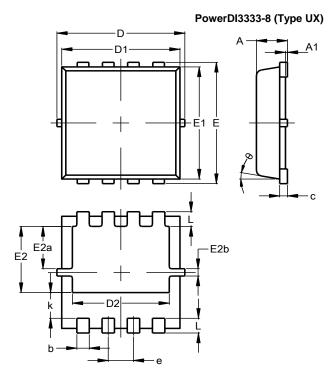






Package Outline Dimensions

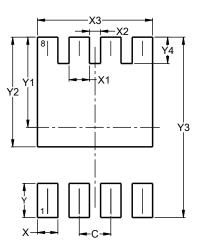
Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI3333-8						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
C	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
E	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E2a	0.95	1.35	1.15			
E2b	0.10	0.30	0.20			
е	0.65 BSC					
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions Value (in mm) 0.650 С Х 0.420 X1 0.420 X2 0.230 Х3 2.370 Υ 0.700 Y1 1.850 Y2 2.250 Y3 3.700 Y4 0.540

PowerDI3333-8 (Type UX)



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